Complementary Silicon Plastic Power Transistors

- . . . designed for use as high-frequency drivers in audio amplifiers.
- DC Current Gain Specified to 4.0 Amperes

 $h_{FE} = 40 \text{ (Min)} @ I_{C} = 3.0 \text{ Adc}$

= 20 (Min) @ I_C = 4.0 Adc

• Collector-Emitter Sustaining Voltage —

VCEO(sus) = 120 Vdc (Min) — MJE15028, MJE15029 = 150 Vdc (Min) — MJE15030, MJE15031

• High Current Gain — Bandwidth Product

 $f_T = 30 \text{ MHz (Min)} @ I_C = 500 \text{ mAdc}$

• TO-220AB Compact Package

MAXIMUM RATINGS

Rating	Symbol	MJE15028 MJE15029	MJE15030 MJE15031	Unit
Collector–Emitter Voltage	VCEO	120	150	Vdc
Collector–Base Voltage	V _{CB}	120	150	Vdc
Emitter–Base Voltage	VEB	5.0		Vdc
Collector Current — Continuous — Peak	IC	8.0 16		Adc
Base Current	ΙΒ	2.0		Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	50 0.40		Watts W/°C
Total Power Dissipation @ T _A = 25°C Derate above 25°C	PD	2.0 0.016		Watts W/°C
Operating and Storage Junction Temperature Range	T _J , T _{Stg}	-65 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.5	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	°C/W

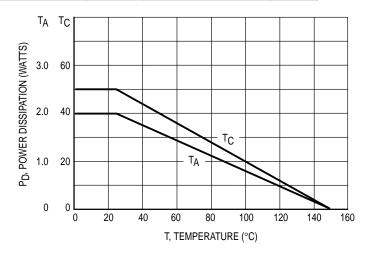


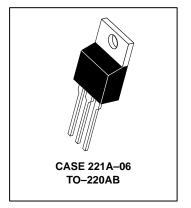
Figure 1. Power Derating

Preferred devices are Motorola recommended choices for future use and best overall value.

MJE15028* MJE15030* MJE15029* MJE15031*

*Motorola Preferred Device

8 AMPERE
POWER TRANSISTORS
COMPLEMENTARY
SILICON
120-150 VOLTS
50 WATTS





ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (1) (I _C = 10 mAdc, I _B = 0)	MJE15028, MJE15029 MJE15030, MJE15031	VCEO(sus)	120 150	_ _	Vdc
Collector Cutoff Current (VCE = 120 Vdc, IB = 0) (VCE = 150 Vdc, IB = 0)	MJE15028, MJE15029 MJE15030, MJE15031	ICEO		0.1 0.1	mAdc
Collector Cutoff Current (V _{CB} = 120 Vdc, I _E = 0) (V _{CB} = 150 Vdc, I _E = 0)	MJE15028, MJE15029 MJE15030, MJE15031	I _{CBO}		10 10	μAdc
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)		l _{EBO}	_	10	μAdc
ON CHARACTERISTICS (1)					
DC Current Gain ($I_{C} = 0.1 \text{ Adc}$, $V_{CE} = 2.0 \text{ Vdc}$) ($I_{C} = 2.0 \text{ Adc}$, $V_{CE} = 2.0 \text{ Vdc}$) ($I_{C} = 3.0 \text{ Adc}$, $V_{CE} = 2.0 \text{ Vdc}$) ($I_{C} = 4.0 \text{ Adc}$, $V_{CE} = 2.0 \text{ Vdc}$)		hFE	40 40 40 20		
DC Current Gain Linearity (VCE From 2.0 V to 20 V, IC From 0.1 A to 3 A) (NPN TO PNP)		hFE		/p 2 3	
Collector–Emitter Saturation Voltage (I _C = 1.0 Adc, I _B = 0.1 Adc)		VCE(sat)	_	0.5	Vdc
Base–Emitter On Voltage (I _C = 1.0 Adc, V _{CE} = 2.0 Vdc)		VBE(on)	_	1.0	Vdc
DYNAMIC CHARACTERISTICS					
Current Gain — Bandwidth Product (2) (I _C = 500 mAdc, V _{CE} = 10 Vdc, f _{test} = 10 MHz)		fΤ	30	_	MHz

⁽¹⁾ Pulse Test: Pulse Width $\leq 300 \,\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

⁽²⁾ $f_T = |h_{fe}| \cdot f_{test}$.

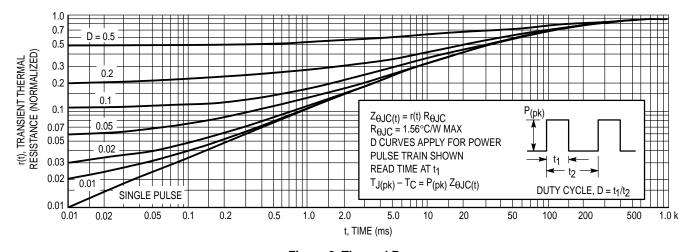


Figure 2. Thermal Response

10 IC, COLLECTOR CURRENT (AMP) 1.0 BONDING WIRE LIMITED THERMALLY LIMITED SECOND BREAKDOWN LIMITED @ T_C = 25°C 0.1 MJE15028 MJE15029= MJE15030 MJE15031 0.02 5.0 20 50 2.0 10 120 150 VCE, COLLECTOR-EMITTER VOLTAGE (VOLTS)

Figure 3. Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation then the curves indicate.

The data of Figures 3 and 4 is based on $T_{J(pk)} = 150\,^{\circ}\text{C}$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} < 150\,^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 2. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

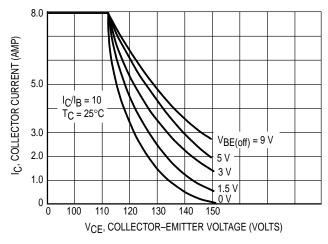


Figure 4. Reverse–Bias Switching Safe Operating Area

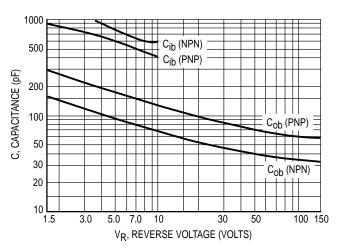


Figure 5. Capacitances

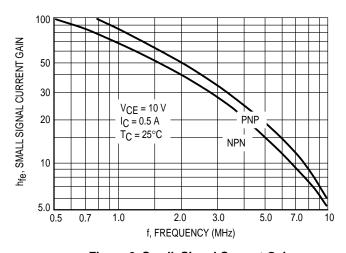


Figure 6. Small-Signal Current Gain

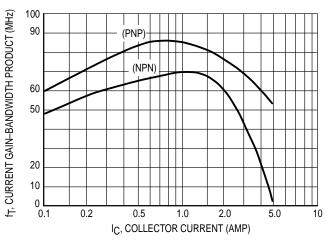
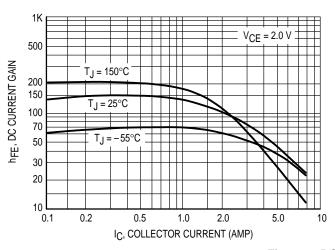


Figure 7. Current Gain-Bandwidth Product



PNP — MJE15029 MJE15031



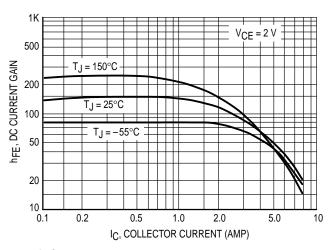
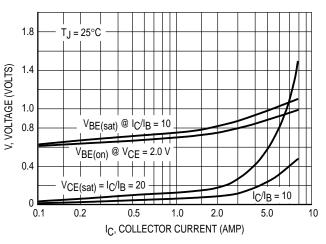


Figure 8. DC Current Gain

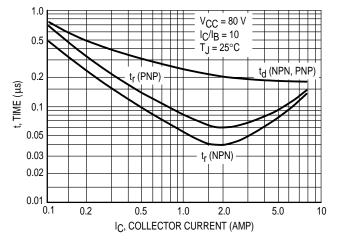
IC, COLLECTOR CURRENT (AMP)

NPN



PNP

Figure 9. "On" Voltage





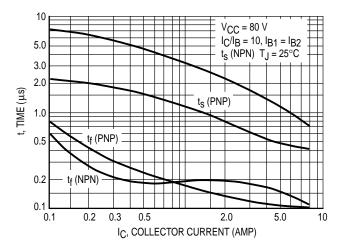
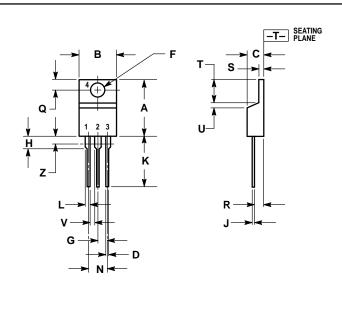


Figure 11. Turn-Off Times

PACKAGE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
ם	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Η	0.110	0.155	2.80	3.93
7	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
ø	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
J	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080	-	2.04

- STYLE 1:
 PIN 1. BASE
 2. COLLECTOR
 3. EMITTER

 - 4. COLLECTOR

CASE 221A-06 TO-220AB **ISSUE Y**

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